



US 20240213250A1

(19) **United States**

(12) **Patent Application Publication**  
**KOH et al.**

(10) **Pub. No.: US 2024/0213250 A1**

(43) **Pub. Date: Jun. 27, 2024**

(54) **SELF-ALIGNED BACKBONE FOR FORKSHEET TRANSISTORS**

(22) Filed: **Dec. 24, 2022**

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**Publication Classification**

(51) **Int. Cl.**  
**H01L 27/092** (2006.01)  
**H01L 29/06** (2006.01)  
**H01L 29/786** (2006.01)

(52) **U.S. Cl.**  
CPC ..... **H01L 27/0924** (2013.01); **H01L 29/0673** (2013.01); **H01L 29/78696** (2013.01)

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(57) **ABSTRACT**

Embodiments disclosed herein include forksheet transistor transistors with self-aligned backbones. In an example, an integrated circuit structure includes a backbone including a lower backbone portion distinct from an upper backbone portion. A first vertical stack of nanowires is in lateral contact with a first side of the backbone. A second vertical stack of nanowires is in lateral contact with a second side of the backbone, the second side opposite the first side.

(21) Appl. No.: **18/088,547**

